

L1200-66-60 epoxy lens type Infrared illuminator

L1200-66-60 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency InGaAsP diode chips, mounted on a metal stem TO-66 with AlN ceramics and covered with double coated clear silicone and epoxy resin.

These devices are designed for high current operation with proper heat sinking to improve thermal conductive efficiency.

◆ Features

- 1) High reliability
- 2) Compact (TO-66) package
- 3) High output power at 1200nm

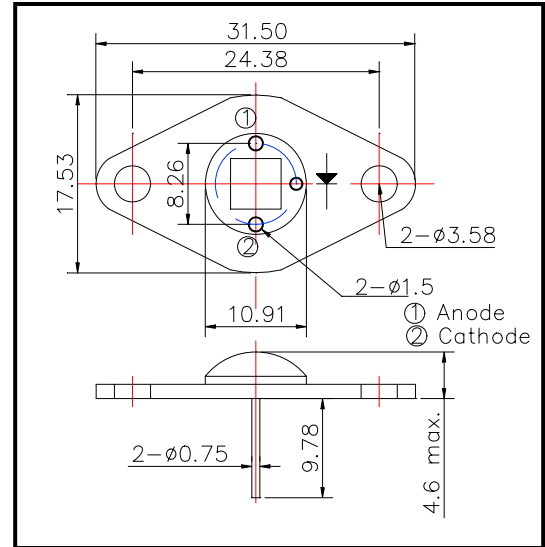
◆ Applications

- 1) For IR search light
- 2) For CCD lighting

◆ Specifications

- 1) Product name IR illuminator
- 2) Spec. No. L1200-66-60
- 3) Chip
 - (1) Material InGaAsP
 - (2) Peak wavelength 1200m
- 4) Package
 - (1) Stem TO-66 stem with AlN
 - (2) Lens Clear silicone and epoxy lens

◆ Outer dimension (Unit: mm)



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temp.
Power Dissipation	PD	5.5	W	Ta=25°C
Forward Current	IF	800	mA	Ta=25°C
Pulsed Forward Current	IFP	5	A	Ta=25°C
Operating Temperature	TOPR	-30 ~ +80	°C	
Storage Temperature	TSTG	-30 ~ +110	°C	
Soldering Temperature	TSOL	240	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=1us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Total Radiated Power	PO	IF=600mA		60		mW
Forward Voltage	VF	IF=600mA		6.0		V
Reverse Current	VR	IR=10uA	30			V
Peak Wavelength	λP	IF=600mA	1150	1200	1250	nm
Half Width	Δλ	IF=600mA		60		nm
Viewing Half Angle	θ 1/2	IF=600mA		±60		deg.
Rise Time	tf	IF=100mA		15		ns
Fall Time	tf	IF=100mA		10		ns

‡Total Radiated Power is measured by Ando Optical Multi Meter AQ2140 & AQ2742.

‡Heat sink is required to protect LED at 60°C or less.